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P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)	
- 100	82 at V _{GS} = - 10 V	- 15	46 nC	

FEATURES

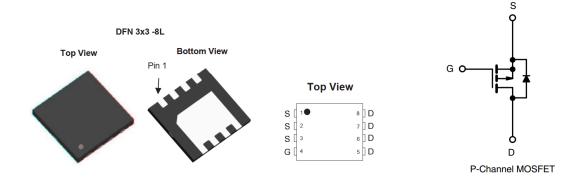
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Low Thermal Resistance



ROHS

APPLICATIONS

· Active Clamp in IntermediateDC/DC Power Supplies



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	- 100			
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 25 °C	1	- 15	А	
	T _C = 100 °C	─ I _D	- 9.4		
Pulsed Drain Current ^b	I _{DM}	- 40			
Single Avalanche Energy		E _{AS}	15	mJ	
Maximum Daylor Discinations	T _C = 25 °C	В	60	W	
Maximum Power Dissipation ^c	T _C = 100 °C	$\overline{}$ P_{D}	24	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	31	°C/W		
Junction-to-Case (Drain)	R _{thJC}	2.08]		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static					•	
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0, I _D = - 250 μA	- 100			V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 2		- 4	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	1	V _{DS} = - 100V, V _{GS} = 0 V		- 1		
	I _{DSS}	V _{DS} = -80V, V _{GS} = 0 V, T _J = 55 °C			- 10	μA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 4 A		82	105	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4 A		23		S
Dynamic ^b					'	
Input Capacitance	C _{iss}			2050		
Output Capacitance	C _{oss}	$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		148		pF
Reverse Transfer Capacitance	C _{rss}	1		125		
Total Gate Charge	Qg			46		
Gate-Source Charge	Q_{gs}	$V_{DS} = -50 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -4 \text{ A}$		6		nC
Gate-Drain Charge	Q_{gd}	1		10		1
Gate Resistance	R _g	f = 1 MHz		4.8		Ω
Turn-On Delay Time	t _{d(on)}			14		
Rise Time	t _r	$V_{DD} = -50 \text{ V, R}_{L} = 1.5 \Omega$		15		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong -4 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 3\Omega$		45		ns
Fall Time	t _f	1		13		1
Drain-Source Body Diode Characterist	ics					
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 15	Α
Pulse Diode Forward Current	I _{SM}				- 40	
Body Diode Voltage	V_{SD}	I _S = - 1 A			- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	- I _F = - 4 A, dl/dt = 100 A/μs, T _J = 25 °C		48		ns
Body Diode Reverse Recovery Charge	Q _{rr}	- 1F 4 Λ, αι/αι - 100 Λ/μs, 1J - 25 C		100		nC

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

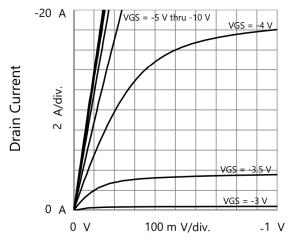
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

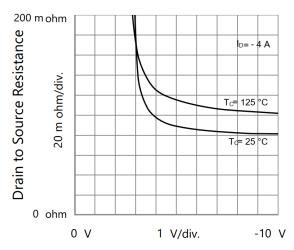




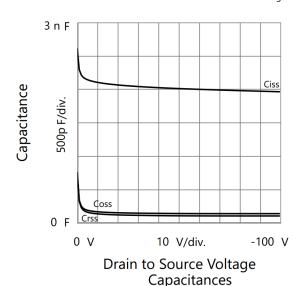
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

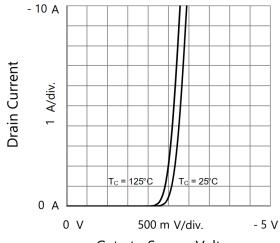


Drain to Source Voltage Output Characteristics

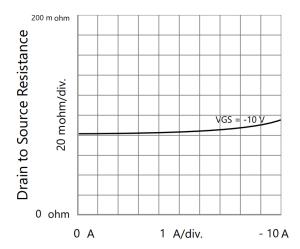


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

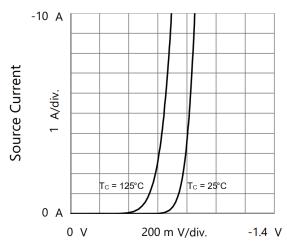




Gate to Source Voltage Transfer Characteristics



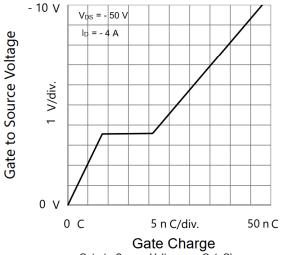
Drain Current
Drain to Source Resistance vs. Drain Current



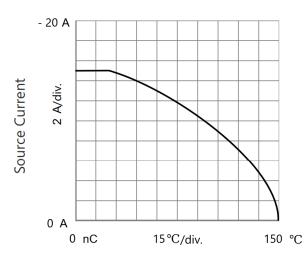
Source to Drain Voltage Body Diode Forward Characteristics



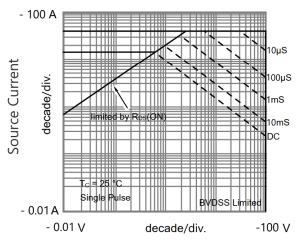
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



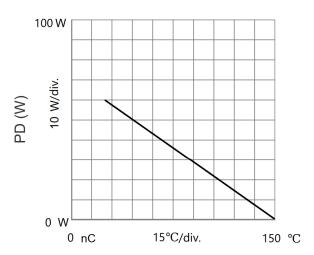
Gate to Source Voltage vs. GateCharge



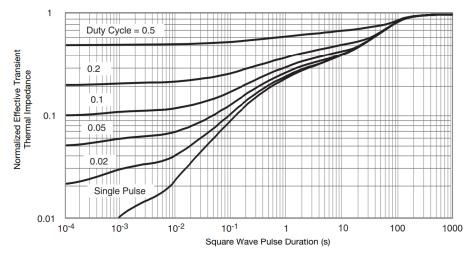
 $T_C \textbf{- Case Temperature}_{\text{Current Derating}}$



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



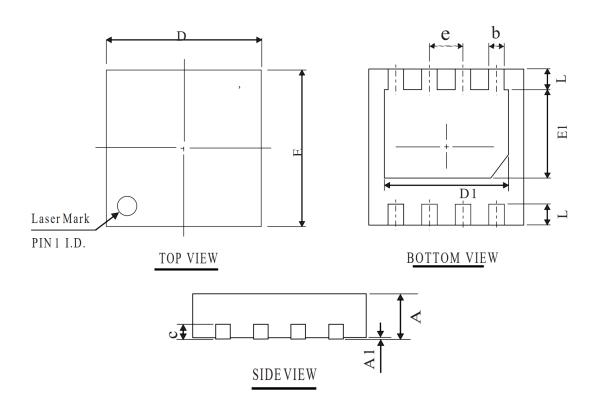
 T_{C} - Case Temperature $_{\text{Power Derating}}$



Normalized Thermal Transient Impedance, Junction-to-Case



DFN3*3-8L PACKAGE OUTLINE



COMMONDIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
Α	0. 60	0.75	0. 90
A1	0. 00	0.02	0. 08
ь	0. 20	0.30	0.45
D	2.85	3.00	3. 15
Е	2. 85	3.00	3. 15
D1	2. 10	2.40	2.70
E1	1.50	1.70	2.00
L	0. 20	0.40	0.60
С	0. 203 REF		
e	0. 65 BSC		

OTHER DIMENSIONS

A	0. 50	0.55	0.60
Α	0.40	0.45	0.50

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